SILICON DIODE CHIPS SD-0013

1. Scope:

This specification applies to silicon switching diode chips, Device No. SD-0013.

2. Structure:

- 2-1. Mesa type.
- 2-2. Electrodes:

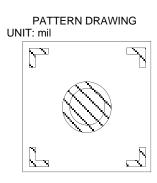
P (Anode) Side: Aluminum alloy. N (Cathode) Side: Gold alloy.

3. Size:

- 3-1. Chip size: 13 mils x 13 mils (0.330 mm x 0.330 mm).
- 3-2. Chip Thickness: 7.5 mils \pm 1.5 mils (0.191 mm \pm 0.038 mm).
- 3-3. Pattern drawing: Refer to the attached drawing.

4. Electrical characteristics (Ta = 25 $^{\circ}$ C)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Forward Voltage	VF	IF=10mA Ee=0mW/cm ²	0.77	0.82	0.87	>
Reverse Current	lr	VR=80V Ee=0mW/cm ²		0.5	1.0	μА
Reverse Breakdown Voltage	V(BV)R	I _R =5μA Ee=0mW/cm ²	100			V



5. Packing and labeling:

5-1. Packing:

Two types can be chosen:

PSA: Sheet type

Each pellet is mounted on an adhesive sheet

With wire-bonded electrode side up.

NS :Sheet type

Each pellet is mounted on an adhesive sheet

With back electrode side up.

5-2. Labeling:

Each lot has a label sheet, writting type, lot no,

PCS, avg., and quantity of good chips.

